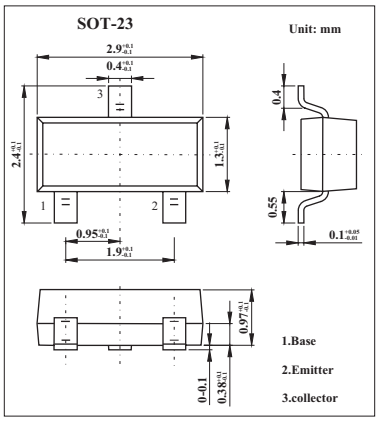
Silicon Transistor

2SA1226



■ Features

- High gain bandwidth product
- Low output capacitance
- Low noise

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage (R_{BE} = ∞)	V_{CBO}	-40	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5.0	V
Collector current - continuous	I_C	-30	mA
Total power dissipation at 25℃ ambient temperature	P_T	200	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = -40V , I_E = 0			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -4.0V , I_C = 0			-0.1	μA
DC current gain	h_{FE}	V_{CE} = -10V , I_C = -1.0mA	40	90	180	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -10mA , I_B = -1.0mA		-0.09	-0.3	V
Base-emitter vVoltage	V_{BE}	V_{CE} = -10V, I_C = -10mA	-0.67	-0.72		V
Gain bandwidth product	f_T	V_{CE} = -10V , I_E = 1.0mA	250	400		MHz
Output capacitance	C_{ob}	V_{CB} = -10V , I_E = 0 , f = 1.0MHz		1.1	2.0	pF
Noise figure	NF	V_{CE} = -10V, I_C = -1.0mA, RG = 500Ω, f = 1.0MHz		3.5		dB

■ h_{FE} Classification

Marking	E2	E3	E4
hFE	40～80	60～120	90～180